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Song et al.

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(54) **LIQUID CRYSTAL DISPLAY DEVICES**

(75) Inventors: **Jun-Ho Song; Kyeong-Nam Lee**, both
of Kyungki-do (KR)

(73) Assignee: **Samsung Electronics Co., Ltd.** (KR)

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patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days.

This patent is subject to a terminal dis-
claimer.

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(22) Filed: **Mar. 12, 2001**

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(63) Continuation of application No. 09/106,226, filed on Jun.
29, 1998, now Pat. No. 6,215,541.

(30) Foreign Application Priority Data

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Feb. 16, 1998 (KR) 98-4562

(51) Int. Cl.⁷ **G02F 1/1343; G02F 1/136**

(52) U.S. Cl. **349/141; 349/42**

(58) Field of Search 349/42, 43, 141,
349/143; 257/59, 72

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Primary Examiner—William L. Sikes

Assistant Examiner—Dung Nguyen

(74) Attorney, Agent, or Firm—Myers Bigel Sibley &
Sajovec

(57) ABSTRACT

A gate wire including a gate line, a gate electrode, a gate pad and a gate line connector and a common signal wire are formed on a substrate, and a gate insulating layer is formed over the gate wire and the common signal wire. A semiconductor layer and an ohmic contact layer are sequentially formed on the gate insulating layer, a data wire including a source and a drain electrode, a data line, a data pad and a data line connector and a pixel electrode are formed thereon. The thickness of the data wire and the pixel electrode is equal to or less than 500 Å. A passivation layer is formed on the data wire and the pixel electrode, a redundant data wire is formed thereon, and a redundant gate pad and a redundant gate line connector are formed. The redundant data wire is electrically connected to the data wire through the contact holes in the passivation layer, and the redundant gate pad and the redundant gate line connector are electrically connected to the gate pad and the gate line connector respectively through the contact holes in the passivation layer and the gate insulating layer. The redundant gate line connector and the redundant data line connector are connected to each other to short the gate and the data wires. After an alignment layer is formed and rubbed, the edge of the panel is cut away to remove the gate line connector and the data line connector.

13 Claims, 23 Drawing Sheets

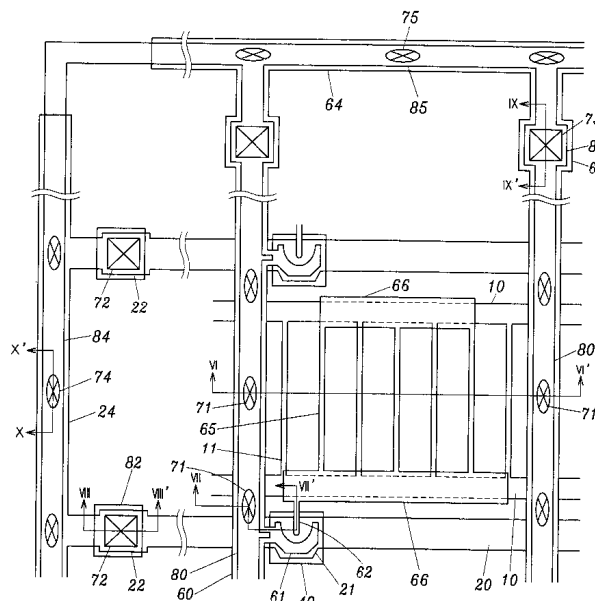


FIG. 3A

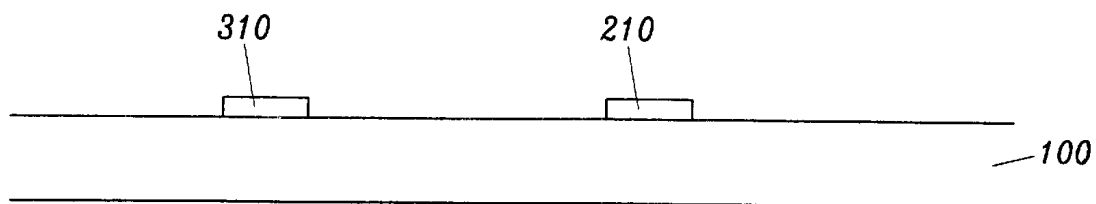


FIG. 3B

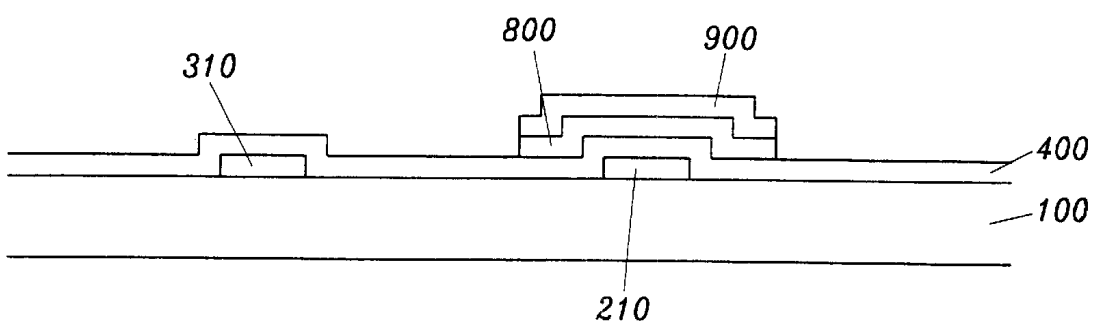


FIG. 3C

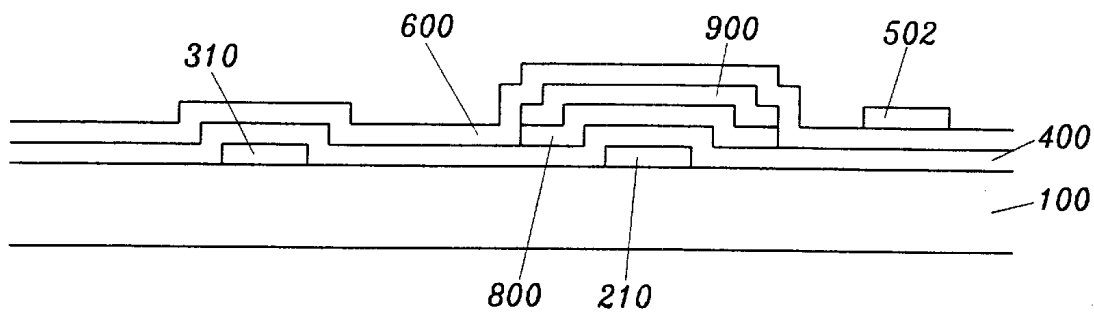


FIG. 3D

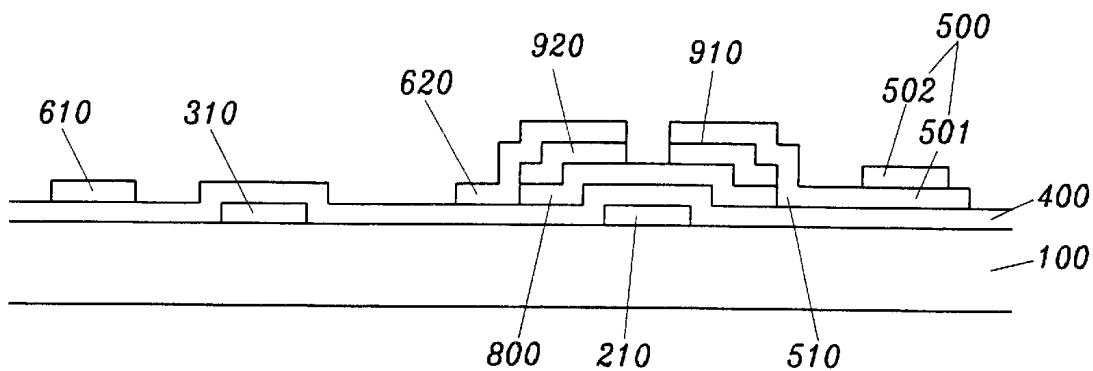


FIG. 4

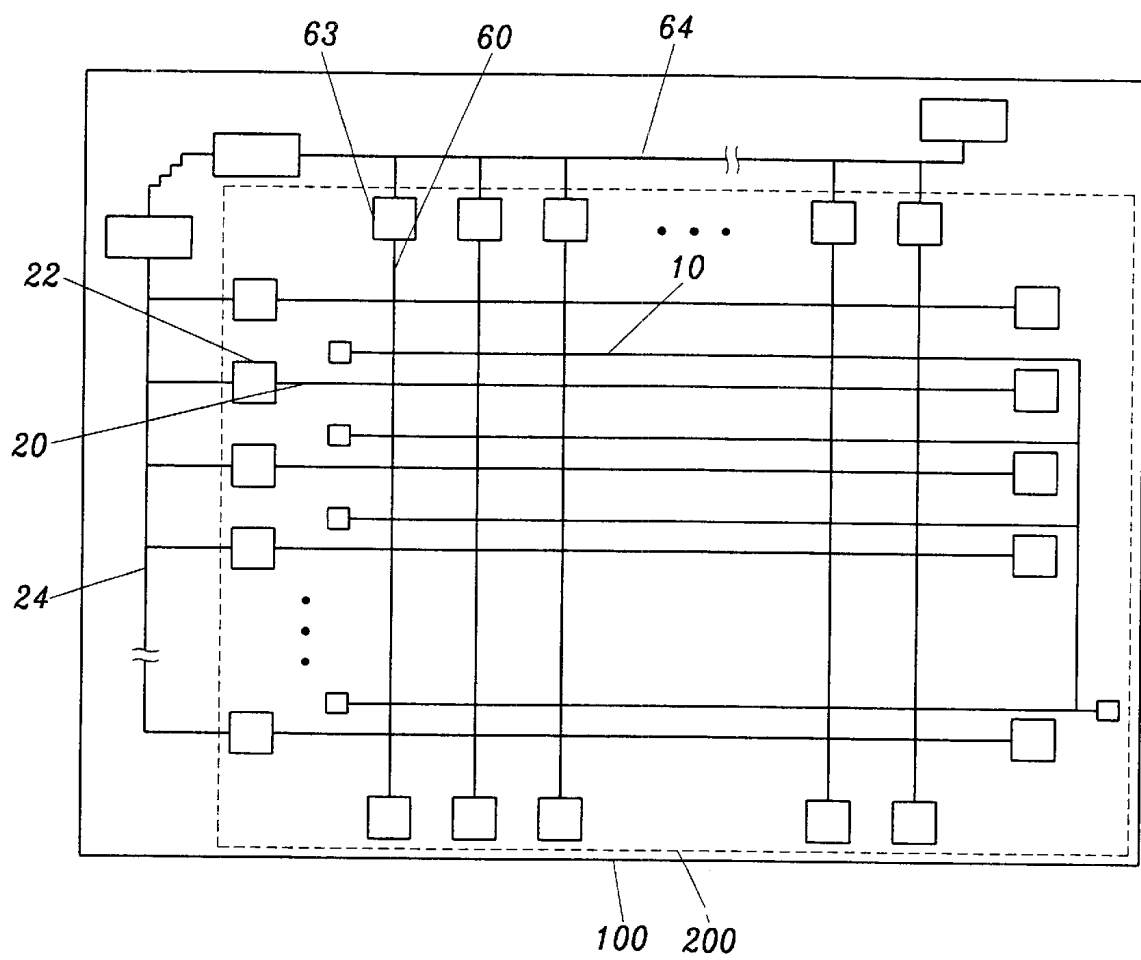


FIG. 6

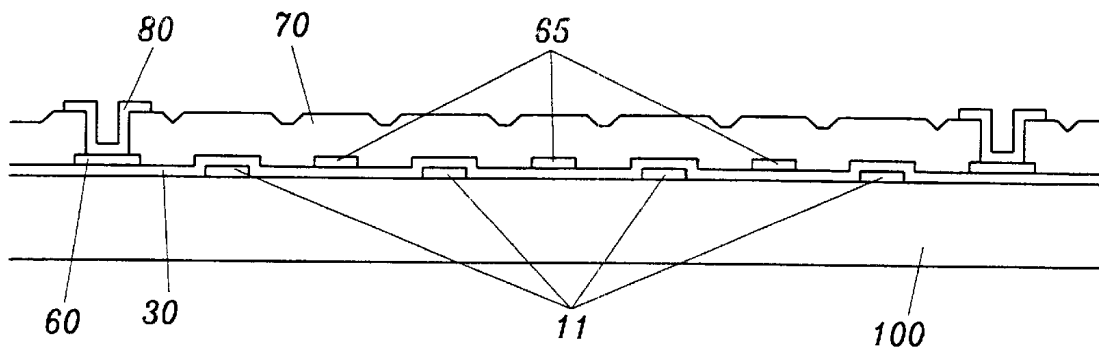


FIG. 7

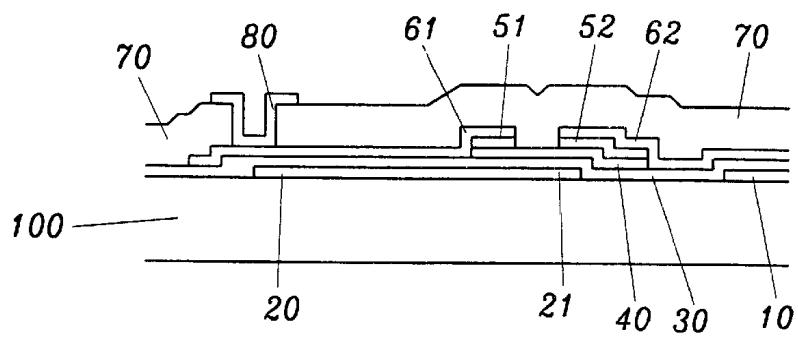


FIG. 8

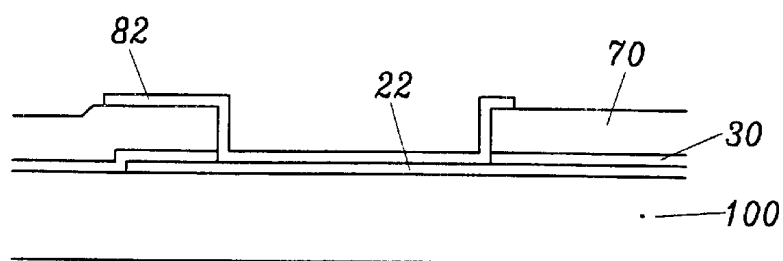


FIG. 9

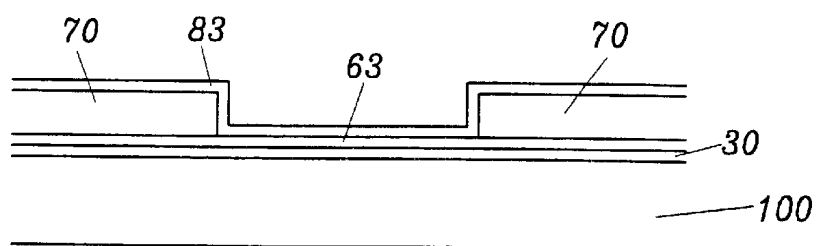


FIG. 10

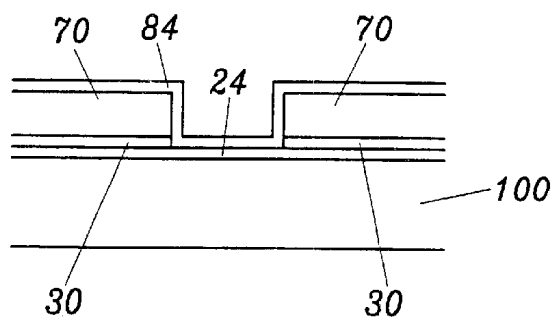


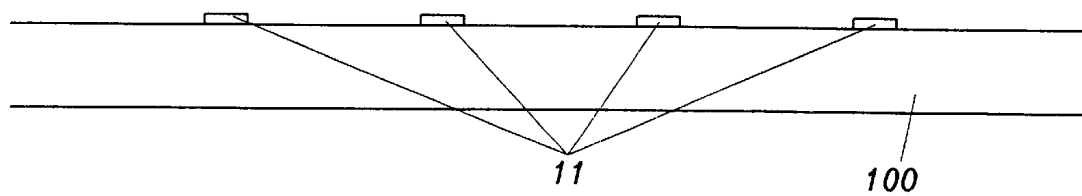
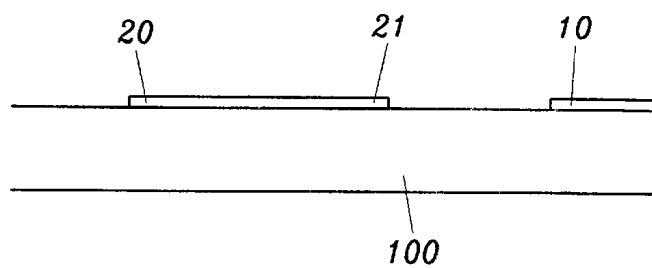
FIG. 11A*FIG. 11B*

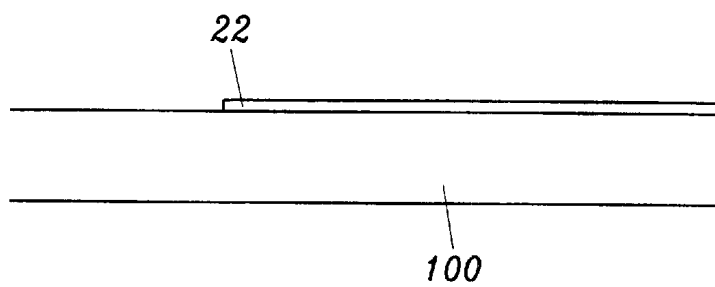
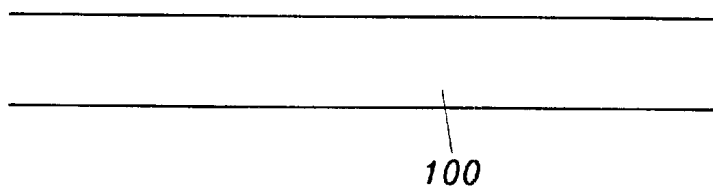
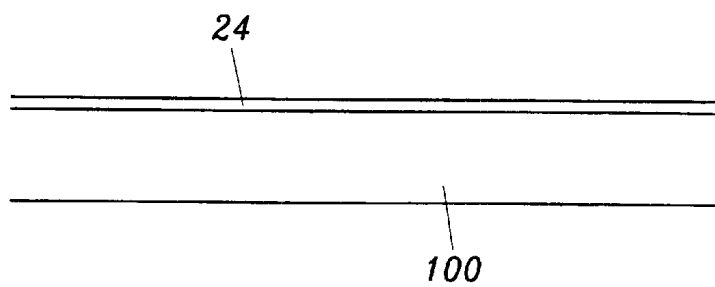
FIG. 11C*FIG. 11D**FIG. 11E*

FIG. 12A

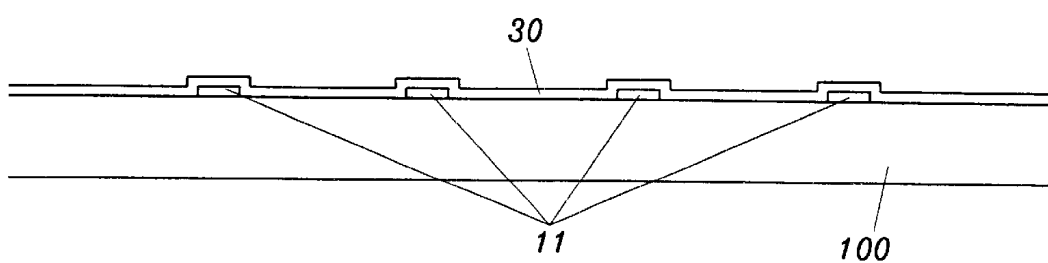


FIG. 12B

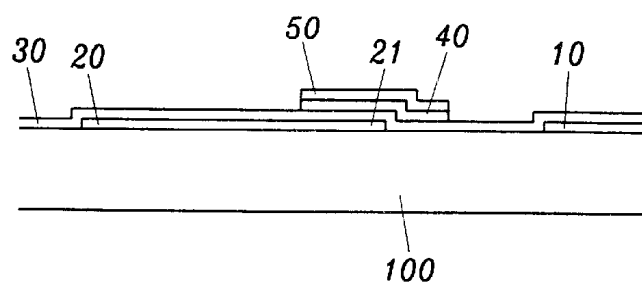


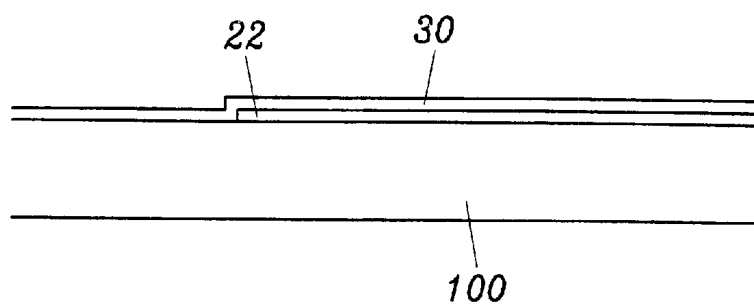
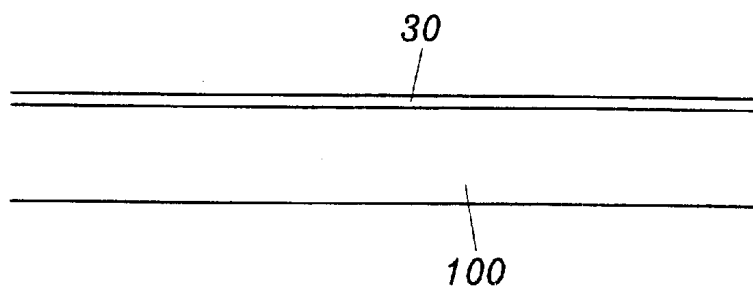
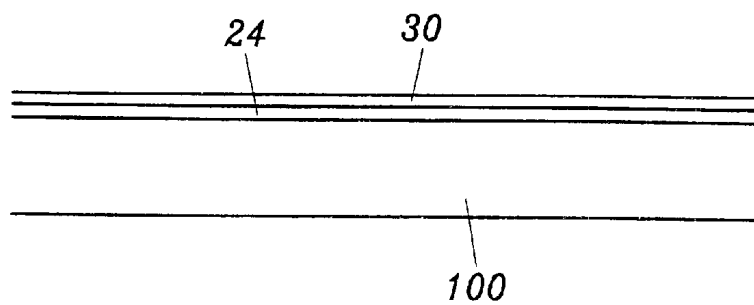
FIG. 12C*FIG. 12D**FIG. 12E*

FIG. 13A

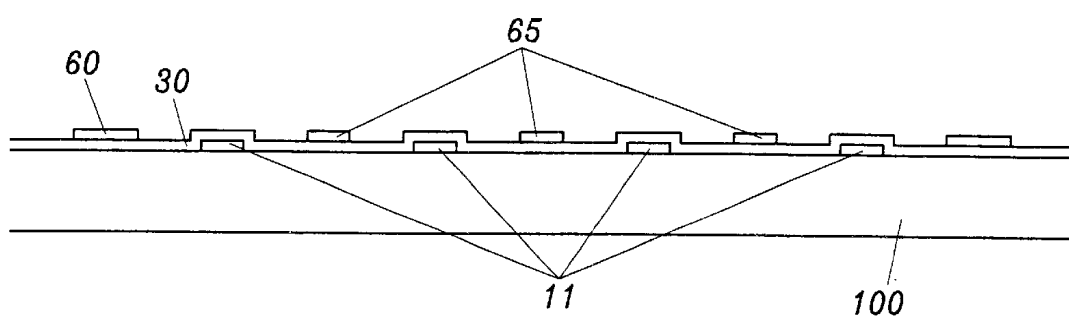


FIG. 13B

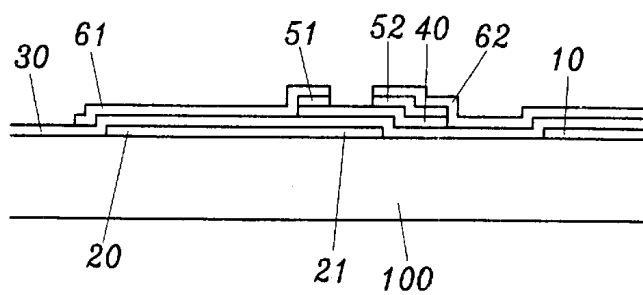


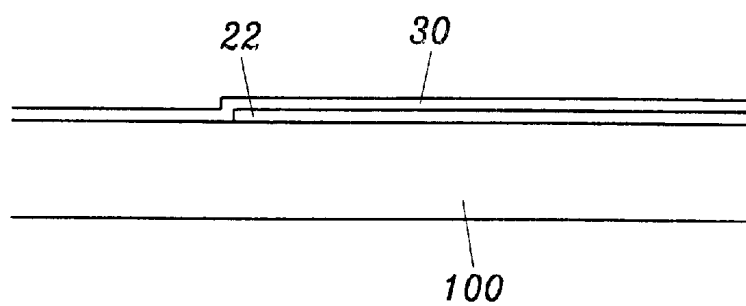
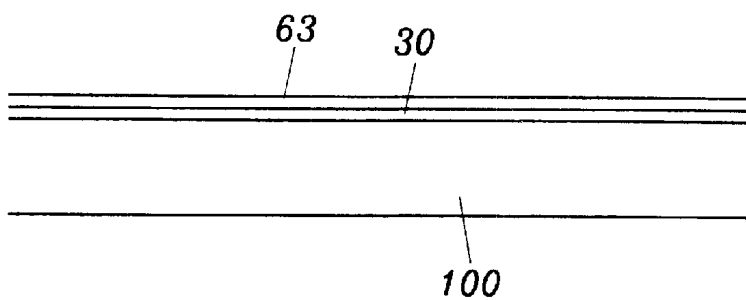
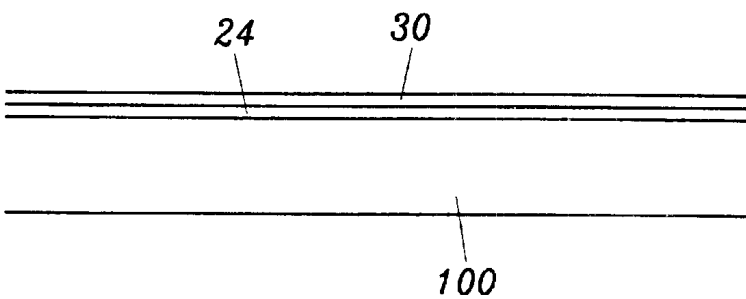
FIG. 13C*FIG. 13D**FIG. 13E*

FIG. 14A

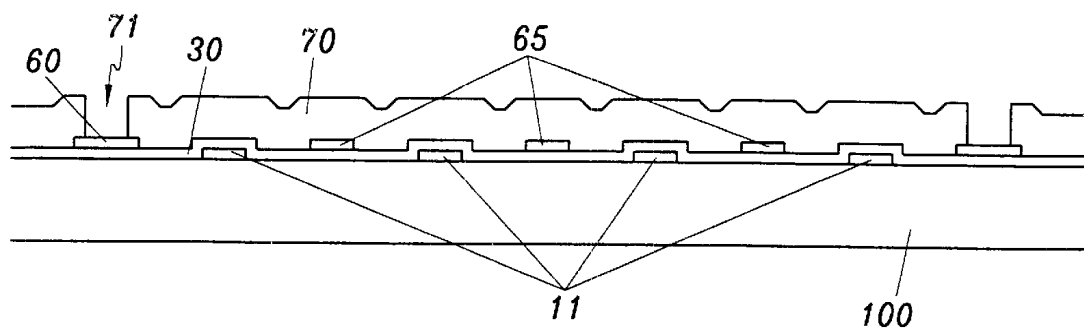


FIG. 14B

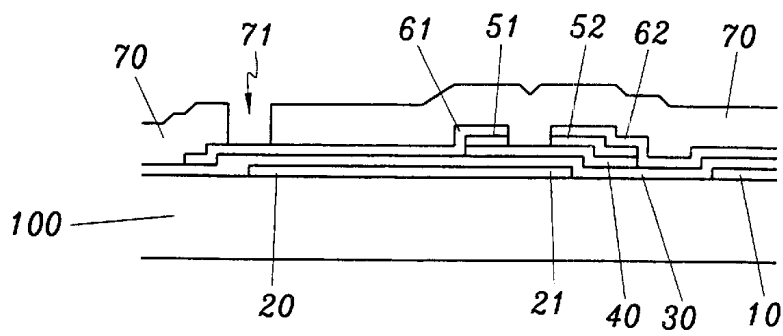


FIG. 14C

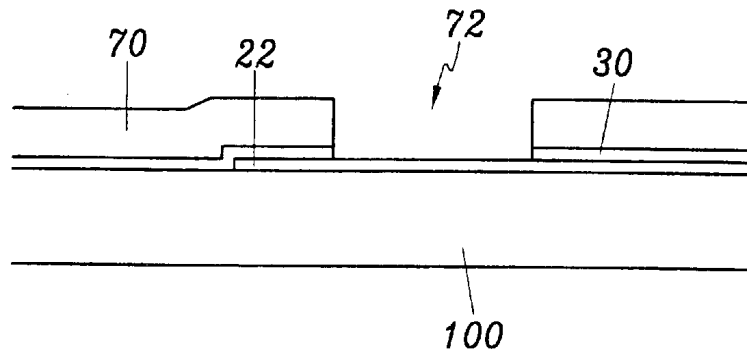


FIG. 14D

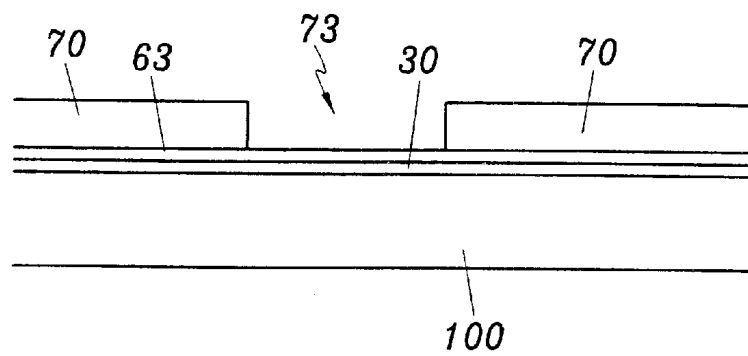


FIG. 14E

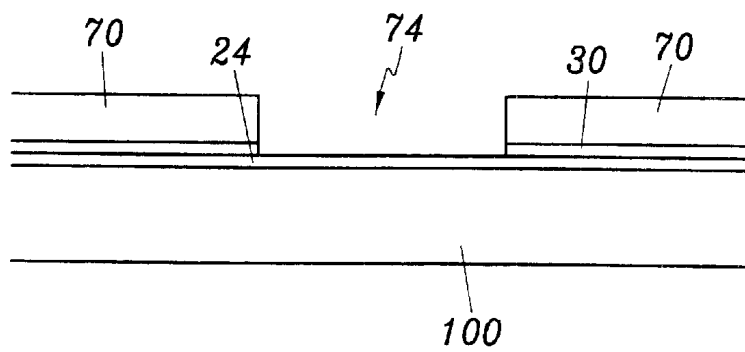


FIG. 15A

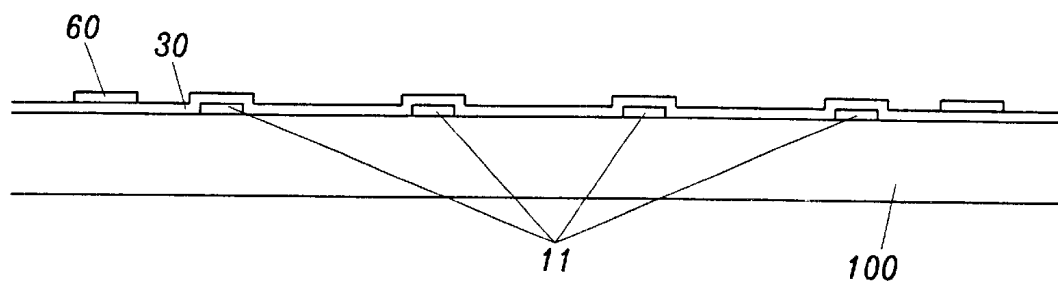


FIG. 15B

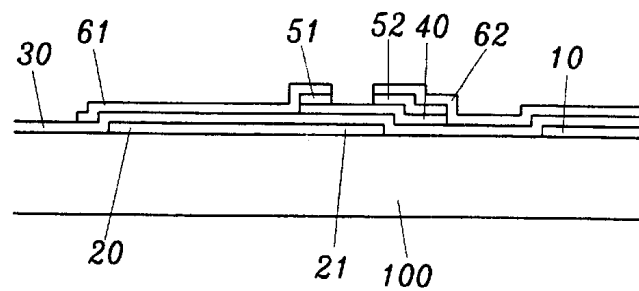


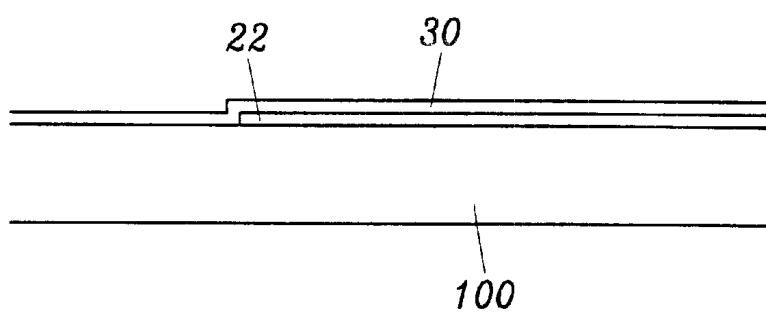
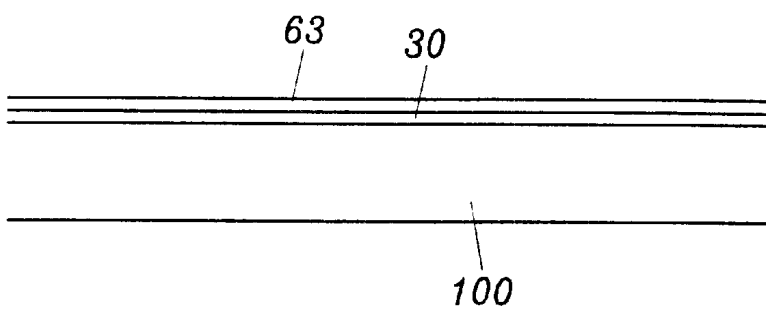
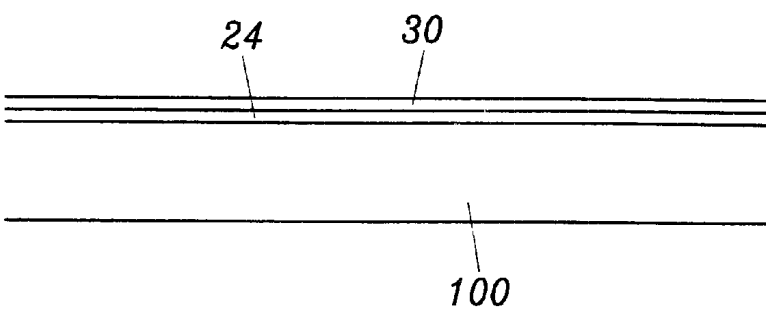
FIG. 15C*FIG. 15D**FIG. 15E*

FIG. 16A

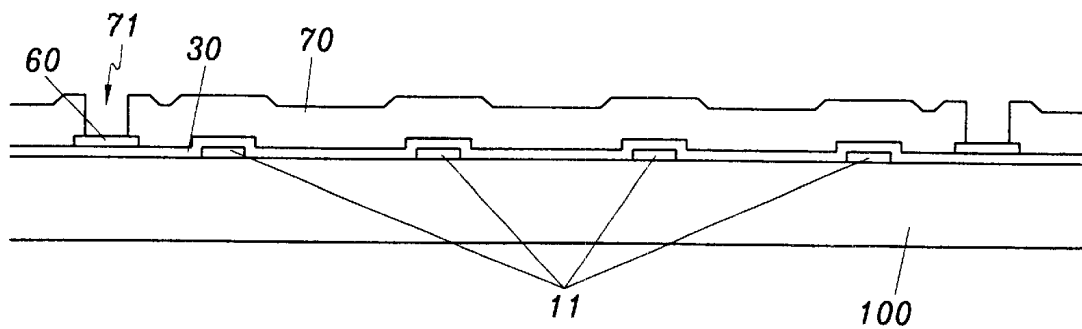


FIG. 16B

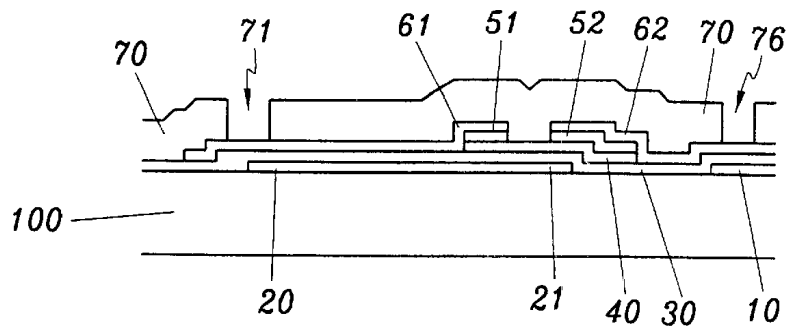


FIG. 16C

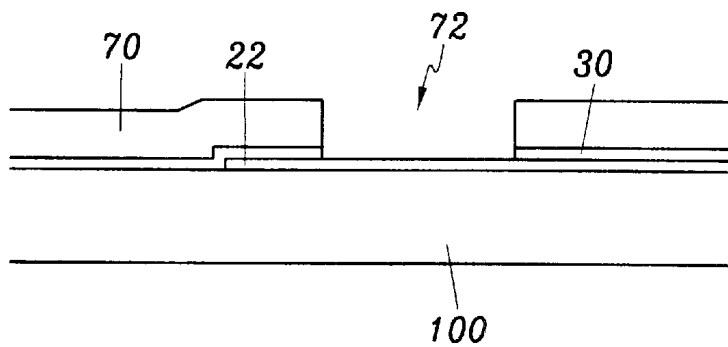


FIG. 16D

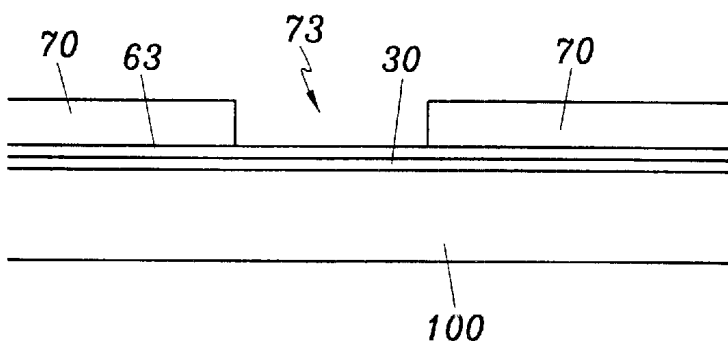


FIG. 16E

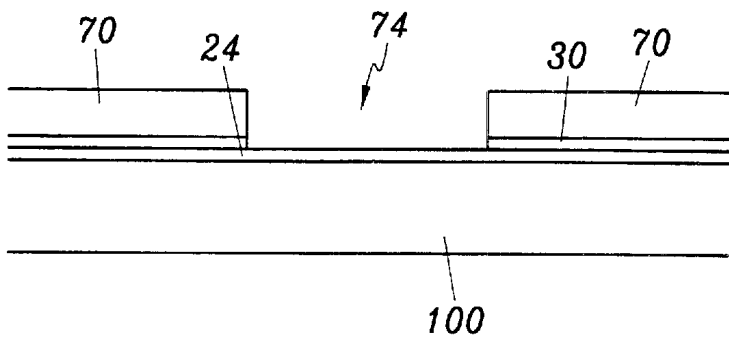


FIG. 17A

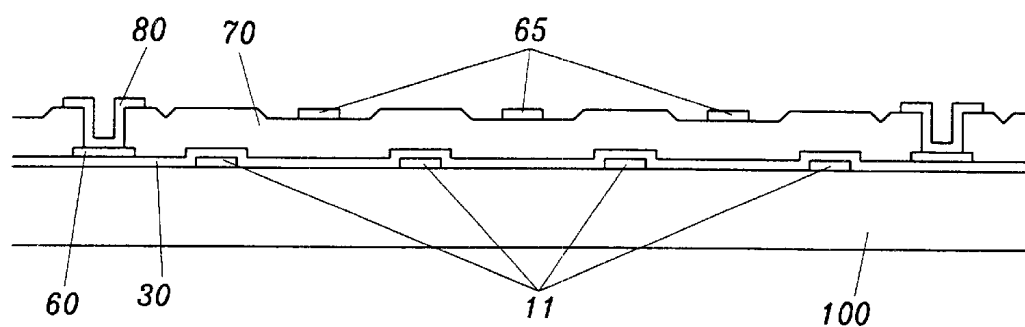


FIG. 17B

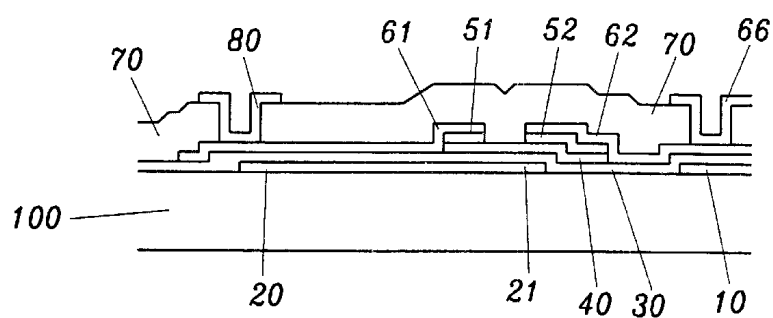


FIG. 17C

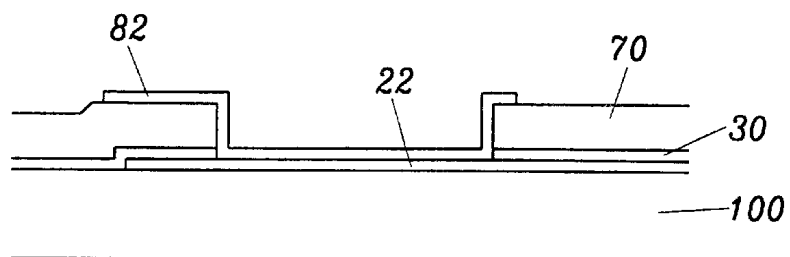


FIG. 17D

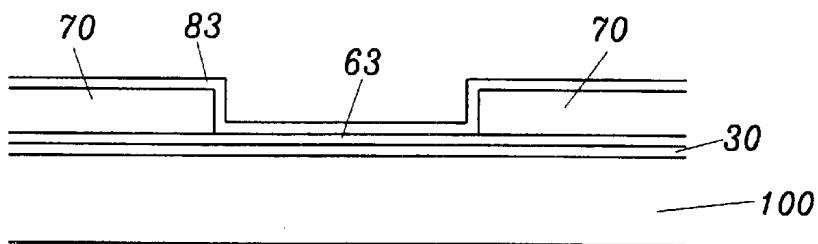


FIG. 17E

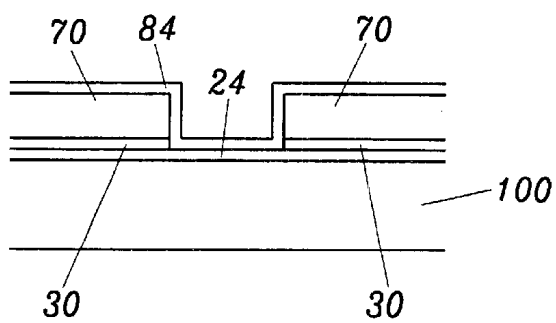


FIG. 19

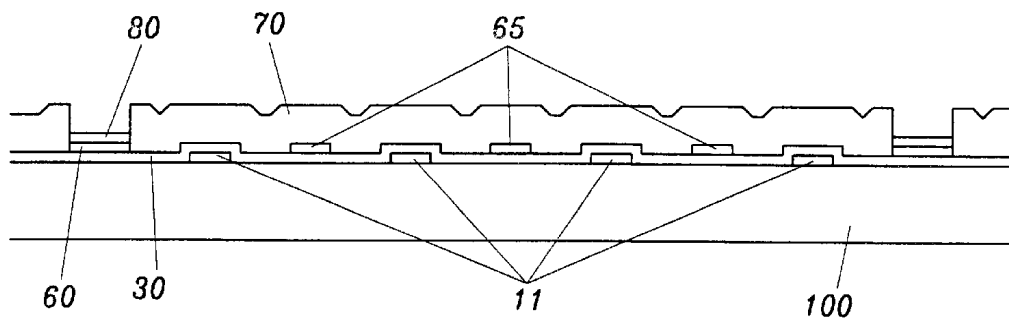


FIG. 20

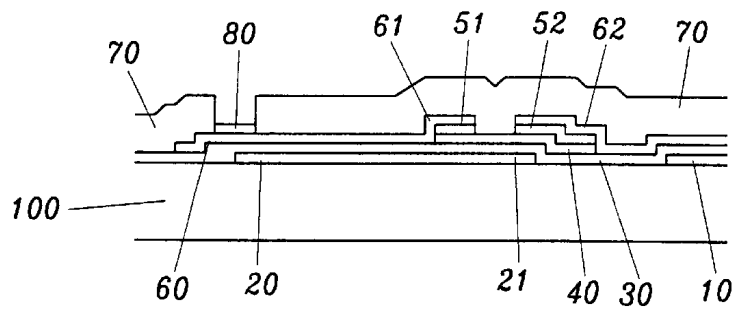


FIG. 21

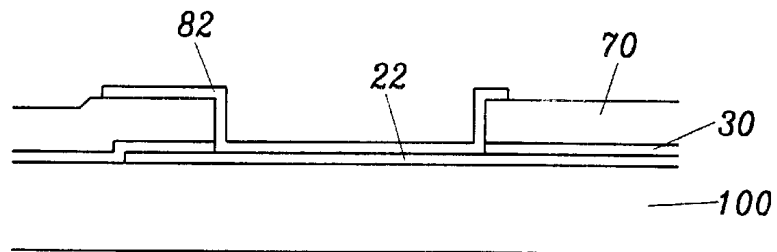


FIG. 22

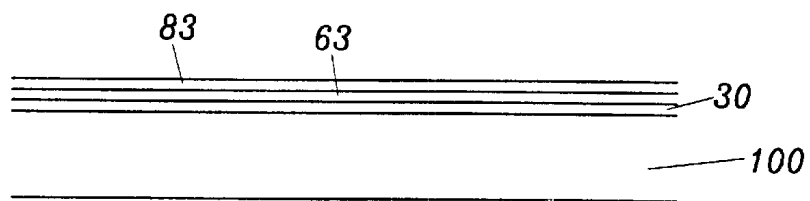
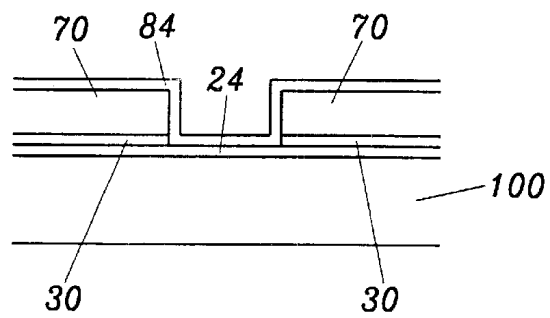


FIG. 23



LIQUID CRYSTAL DISPLAY DEVICES

This application is a continuation of prior application Ser. No. 09/106,226, now U.S. Pat. No. 6,215,541 filed Jun. 29, 1998, the disclosure of which is hereby incorporated herein by reference.

BACKGROUND OF THE INVENTION

(a) Field of the Invention

The present invention relates to liquid crystal displays and manufacturing methods thereof, more specifically to liquid crystal displays having electrode arrays for applying electric fields parallel to substrates and thin film transistors as switching elements and manufacturing methods thereof.

(b) Description of the Related Art

A liquid crystal display (LCD) having an electrode array for generating an electric field which is parallel to substrates (IPS mode; in-plane switching mode) is disclosed in U.S. Pat. No. 5,598,285 of Kondo et al.

The IPS mode LCD of Kondo et al. has two substrates opposite each other and a liquid crystal layer therebetween. Two kinds of electrodes for generating electric field, common electrodes and pixel electrodes are formed on one of the substrates. An alignment layer is coated on the electrodes.

However, since the two kinds of electrodes are made of different layers and have different thickness, the surface of the alignment layer may not be flat, and this causes non-uniform rubbing which may result in light leakage.

Moreover, the liquid crystal display of Kondo et al., in particular, transistors of the liquid crystal display are easily defected by the electrostatic discharge because the two electrodes are formed together on a single substrate.

For electrostatic discharge protection, all wires may be short-circuited during the manufacturing process and separated after the manufacture of the panel is completed. However, this method is complicated.

SUMMARY OF THE INVENTION

In view of the above, it is an object of the present invention to reduce the light leakage of IPS mode liquid crystal displays.

It is another object of the present invention to prevent thin film transistors from being destroyed by the electrostatic discharge.

It is another object of the present invention to simplify the manufacturing process of IPS mode liquid crystal displays.

It is another object of the present invention to decrease the opening of wires.

It is another object of the present invention to increase the reliability of the contacts between pads and drivers.

These and other objects, features and advantages are provided, according to the present invention, by forming a pixel electrode using a thin single conductive layer, and a data line is formed as a double layer.

The thickness of the single conductive layer forming a pixel electrode may be equal to or less than 1,000 Å. It is more preferable that the thickness of the single conductive layer is equal to or less than 500 Å. The double layer forming a data line may include a lower layer, which is the same as the pixel electrode, and an upper layer having a low resistivity of 15 $\mu\Omega\text{cm}$ or less. The single layer or the lower layer of the double layer may be formed using a metal having a low resistivity of 15 $\mu\Omega\text{cm}$ or less, and the upper layer may be formed by a pad material which is not easily broken in the manufacturing process.

A passivation layer which is thick relative to the pixel wire may have relatively flat surface since the pixel wire is relatively thin. The flat surface may give rise to uniform rubbing and thus the light leakage may be reduced.

These and other objects, features and advantages are also provided, according to the present invention, by forming a common signal wire and a gate wire including a gate line, a gate electrode a gate pad and a gate line connector on a substrate, forming a gate insulating layer over the common signal wire and the gate wire, forming a channel layer and an ohmic contact layer thereon, forming a pixel electrode and a data wire including a source and a drain electrodes, a data line, a data pad and a data line connector using a first conductive layer, forming a passivation layer on the data wire and the pixel electrode, forming a redundant data wire including a redundant data line, a redundant data pad and a redundant data line connector, a redundant gate pad and a redundant gate line connector using a second conductive layer. The redundant data wire is electrically connected to the data wire through the contact holes formed in the passivation layer. The redundant gate pad and the redundant gate line connector are connected to the gate pad and the gate line connector respectively through the contact holes formed in the gate insulating layer and the passivation layer. The redundant gate line connector and the redundant data line connector are connected with each other to short-circuit the gate lines and the data lines on the substrate.

After forming the panel, an alignment layer is printed and rubbed, and the gate line connector and the data line connector are removed by cutting out the edge of the panel.

The pixel electrode may be formed in the step of forming redundant data wire using the second conductive layer instead of the first conductive layer, and the thickness of the pixel electrode may be equal to or less than 500 Å.

The redundant data wire may be formed as a single or a double layer, and the single layer or the upper layer of the double layer may be formed using a pad material which is not easily broken in the manufacturing process.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a layout view of a panel for a liquid crystal display according to the first embodiment of the present invention.

FIG. 2 shows a cross-sectional view of the panel illustrated in FIG. 1 taken along the line II-II'.

FIGS. 3A-3D are cross-sectional views of the intermediate structures of the panel shown in FIGS. 1 and 2 in the manufacturing steps.

FIG. 4 is a schematic diagram of the LCD panel according to the second embodiment of the present invention.

FIG. 5 shows a layout view of a panel for a liquid crystal display according to the second embodiment of the present invention.

FIGS 6-10 are cross-sectional views of the panel shown in FIG. 5 taken along the lines VI-VI', VII-VII', VIII-VIII', IX-IX' and X-X' respectively.

FIGS. 11A-14E are cross-sectional views of the intermediate structures of the panel shown in FIGS. 4-10 in the manufacturing steps.

FIGS. 15A-17E are cross-sectional views of the intermediate structures of the panel for a liquid crystal display according to another embodiment of the present invention.

FIG. 18 shows a layout view of a panel for liquid crystal display according to another embodiment of the present invention.

FIGS. 1–23 are cross-sectional views of the panel shown in FIG. 18 taken along the lines XIX–XIX', XX–XX', XXI–XXI', XXII–XXII' and XXIII–XXIII' respectively.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

The present invention will now be described more fully hereinafter with reference to the accompanying drawings, in which preferred embodiments of the present invention are shown. This invention may, however, be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the invention to those skilled in the art. In the drawings, the thickness of layers and regions are exaggerated for clarity.

First, the structure of a panel for a liquid crystal display according to the first embodiment of the present invention will be described. FIG. 1 is a layout view of a panel, and FIG. 2 is a cross-sectional view of the panel illustrated in FIG. 1 taken along the line II–II'.

A gate wire including a transverse gate line 200 and a gate electrode 210 which is a branch of the gate line 200 is formed on a substrate 100. A common signal wire including a common signal line 300 parallel to the gate line 200 and a plurality of linear common electrodes 310 connected to the common signal line 300 is also formed on the substrate 100. The common electrodes 310 extend toward the gate line 200, and they are spaced apart from each other and parallel to each other.

A gate insulating layer 400 is formed over the gate wire 200 and 210 and the common signal wire 300 and 310.

A channel layer 800 and an ohmic contact layer 910 and 920 are sequentially formed on a portion of the gate insulating layer 400 over the gate electrode 210. The ohmic contact layer has two portions 910 and 920 separated from each other with respect to the gate electrode 210. A longitudinal data line 500 are formed on the gate insulating layer 300, and a source electrode 510, a branch of the data line 500 extending to the gate electrode 210, is formed on one portion 910 of the ohmic contact layer. The data line 500 intersects the gate line 200 near the gate electrode 210, and has a double-layered structure including a lower chromium layer 501 of about 500 Å and an upper aluminum layer 502 of about 2,000 Å, while the gate electrode 210 has a single chromium layer. On the gate insulating layer 400, a pixel wire including a transverse pixel electrode line 600 and a plurality of pixel electrodes 610 which are branches of the pixel electrode line 600 extending toward the common signal line 300 is also formed between the gate line 20 and the common electrode line 300. The pixel electrodes 610 and the common electrodes 310 are parallel and spaced apart. A drain electrode 620, which is connected to an end portion of the pixel electrode line 600, is formed on the other portion 920 of the ohmic contact layer. The pixel wire 600 and 610 and the drain electrode 620 are formed of a single chromium layer of about 500 Å.

A passivation layer 700 is formed over the pixel wire 600 and 610, the data line 500, the source and the drain electrodes 510 and 620.

Since the data line 500 has a double-layered structure, although the pixel wire 600 and 610 is relatively thin, for example, has thickness of around 500 Å, the data line 500 may not be easily opened. Accordingly, the passivation layer 700 which is thick relative to the pixel wire 600 and 610 may have relatively flat surface. The flat surface may give rise to

uniform rubbing and thus the light leakage may be reduced. The measured contrast ratio of the liquid crystal display according to the first embodiment of the present invention is about 120, while that in the conventional liquid crystal displays is about 60.

The thickness of the pixel wire 600 and 610 may be equal to or less than 1,000 Å, and that of the passivation layer 700 may be 2,000–4,000 Å such that the passivation layer 700 has a relatively flat surface. It is more preferable that the thickness of the pixel wire 600 and 610 is equal to or less than 500 Å. Although the small thickness of the pixel wire 600 and 610 may cause relatively large resistance, it may be allowed for the LCD.

The lower layer 501 and the upper layer 502 forming the data line 500 are not restricted to chromium and aluminum respectively. The lower layer 501 may be made of a conductive material having low resistivity of 15 μΩcm or less, and the upper layer 502 may be made of a pad material which is not easily broken in the manufacturing process.

Now, a manufacturing method of the panel according to the first embodiment of the present invention will be described. FIGS. 3A–3D are cross-sectional views of the intermediate structures of the panel shown in FIGS. 1 and 2 in the manufacturing steps.

A metal layer is deposited and patterned to form a gate wire 200 and 210 and a common signal wire 300 and 310, as shown in FIG. 3A.

A gate insulating layer 400, an intrinsic amorphous silicon layer 800 and a doped amorphous silicon layer 900 are deposited in sequence, and as shown in FIG. 3B, the intrinsic and the doped amorphous silicon layers are patterned together.

A chromium layer 600 of around 500 Å and an aluminum layer of around 2,000 Å are deposited in sequence. As shown in FIG. 3C, the aluminum layer is patterned to form an upper layer 502 of a data line 500. Next, as shown in FIG. 3D, the chromium layer 600 is patterned to form a lower layer 501 of the data line 500, a source electrode 510, a drain electrode 620 and a pixel wire 600 and 610. The doped amorphous silicon layer 900 is etched to form an ohmic contact layer 910 and 920 using the source and the drain electrodes 510 and 620 and the data line 500 as a mask. A passivation layer 700 is deposited thereon, as shown in FIG. 2.

Now, the second embodiment of the present invention is described, where a pixel wire and a data wire have small thickness and a relatively thick redundant data pattern connected to the data wire is provided on a passivation layer.

First, the structure of the panel for a liquid crystal display according to the second embodiment will be described. FIG. 4 is a schematic diagram of the LCD panel according to the second embodiment.

As shown in FIG. 4, a plurality of gate lines 20 extending in a transverse direction are formed on a substrate 100, and a plurality of common signal lines 10 on the substrate 100 are arranged parallel to the gate lines 20. A plurality of gate pads 22, which are connected to external gate drivers (not shown), are formed to be connected to the ends of the gate lines 20. A gate line connector 24 is formed in a longitudinal direction and connected to the gate pads 22 via its branches. A plurality of data lines 60 extending in the longitudinal direction intersect and are insulated from the gate lines 20 and the common signal lines 10. A plurality of data pads 63, which are connected to external data drivers (not shown), are formed to be connected to the ends of the data lines 60. A data line connector 64 is formed in the transverse direction and connected to the data pads 63 via its branches. The gate

line connector **24** and the data line connector **64** are connected to each other so that all the wires including the gate lines **20** and the data lines **60** on the substrate **100** are short-circuited.

This structure causes the electrostatic charges generated during the manufacturing process to be spread over the substrates, thereby protecting thin film transistors effectively. When manufacture of the panel is completed, the wires are separated by cutting out the gate and the data line connectors **24** and **64** along the dotted line **200** in FIG. 4.

In the meantime, a pixel region is defined by the gate lines **20** and the data lines **60**, and the substrate **100** includes a plurality of pixels. A linear pixel electrode and a linear common electrode, not shown in FIG. 4, are formed alternately in the pixel region, and a thin film transistor connected to the gate line, the data line and the pixel electrode is also formed in the pixel region.

Now, the structure of the panel according to the second embodiment will be more fully described. FIG. 5 shows a layout view of a panel for a liquid crystal display according to the second embodiment of the present invention. FIGS. 6 to **10** are cross-sectional views of the panel shown in FIG. 5 taken along the lines VI-VI', VII-VII', VIII-VIII', IX-IX' and X-X' respectively.

As shown in FIGS. 5-10, a plurality of gate lines **20** extending in a transverse direction are formed on a transparent insulating substrate **100**. The end portions of the gate lines **20** are enlarged to form gate pads **22**, and several portions of the gate lines **20** serve as gate electrodes **21**. A gate line connector **24** extending in a longitudinal direction is formed on the substrate **100** and connected to the gate pads **22** via its branches. A pair of common signal lines **10** and a plurality of spaced apart linear common electrodes **11** connected to both the common signal lines **10** are formed between the gate lines **20** on the substrate **100**. The common electrodes **11** extend in the longitudinal direction and are parallel to each other.

A gate insulating layer **30** made of insulator such as silicon nitride is formed over a gate wire **20**, **21**, **22** and **24** and a common signal wire **10** and **11**.

A plurality of channel layers **40** made of semiconductor such as amorphous silicon are formed on portions of the gate insulating layer **30** over the gate electrodes **21**. A plurality of ohmic contact layers **51** and **52** made of a material reducing the contact resistance between the channel layers **40** and wires thereon such as heavily doped amorphous silicon are formed on the amorphous silicon layers **40**, and each ohmic contact layer is divided into two portions **51** and **52** with respect to the gate electrode **21**.

A plurality of data lines **60** are formed on the gate insulating layer **30** and extend longitudinally. The end portions of the data lines **60** are enlarged to form a plurality of data pads **63**. A plurality of source electrodes **61** connected to the data lines **60** and drain electrodes **62** are formed on the respective portions of the ohmic contact layers **51** and **52**. A pair of the pixel electrode lines **66** are formed on the gate insulating layer **30** and overlap the common signal lines **10**. Linear pixel electrodes **65** connected to both the pixel electrode lines **66** are also formed on the gate insulating layer **30** and each pixel electrode **65** is placed between adjacent two of the common electrodes **11**. A transverse data line connector **64** is formed on the gate insulating layer **30** and connected to the data pads **63** via its branches.

The gate electrode **21**, the gate insulating layer **30**, the amorphous silicon layer **40**, the ohmic contact layer **51** and

52, and the source and the drain electrodes **61** and **62** form a thin film transistor for switching the display signals from the data line **60** responsive to the scanning signal from the gate line **10**. The source electrode **61** is U-shaped while the drain electrode **62** is linear. The end of the drain electrode **62** is placed pointing towards the convex part of the source electrode **61**. This arrangement of the source and the drain electrodes **61** and **62** enlarge the on current of the TFT.

A passivation layer **70** made of silicon nitride or the like is formed over the thin film transistor and the remaining data wire **60**, **63**, **64** and **65**. The passivation layer **70** has contact holes **71**, **73** and **75** which expose the mid-portions of the data line **60**, the data pad **63** and the data line connector **64** respectively. In addition, the passivation layer **70** and the gate insulating layer **30** have contact holes **72** and **74** exposing the gate pads **22** and the gate line connector **24**.

A conductor pattern **80** and **83** which has the similar shape to the data wire **60** and **63** is formed on the passivation layer **70** and connected to the data wire **60** and **63** through the contact holes **71** and **73** in the passivation layer **70**. Therefore, the conductor pattern **80** and **83** functions as a redundant data wire. Another conductor pattern having a transverse portion **85** and a longitudinal portion **84** connected to each other is formed on the passivation layer **70**. The transverse portion **86** has branches connected to the conductor pattern **83** and connected to the data line connector **64** via the contact holes **75**, and the longitudinal portion **84** is connected to the gate line connector **24** through the contact holes **74**. Conductor patterns **82** are also formed on the passivation layer **70** and connected to the gate pads **22** through the contact holes **72**.

A manufacturing method of a panel for a liquid crystal display according to the second embodiment of the present invention will be now described. FIGS. 11A-14E are cross-sectional views of the intermediate structures of the panel shown in FIGS. 4-10 in the manufacturing steps. The manufacturing method according to the second embodiment uses 5 masks. The figures to having the view numbers including the capital letters A, B, C, D and E following Arabic numerals correspond to the FIGS. 6-10, respectively.

First, as shown in FIGS. 11A-11E, a metal layer of 3,000 Å is deposited and patterned using a first mask to form a gate wire including a gate line **20**, a gate electrode **21**, a gate pad **22** and a gate line connector **24** and a common signal wire including a common signal line **10** and common electrodes **11**. The gate wire and the common signal wire may be a single layer of chromium, aluminum, aluminum alloy, or molybdenum, etc., or may have a double-layered structure composed of two metal layers.

As shown in FIGS. 12A-12E, a gate insulating layer **30** made of silicon nitride or organic insulating material, etc., a hydrogenated amorphous silicon layer **40** and an n+ hydrogenated amorphous silicon layer **50** heavily doped with n type impurities such as phosphorous are deposited in sequence. The thickness of the three layers are 3,000-5,000 Å, 500-2,000 Å and 500 Å, respectively. The doped amorphous silicon layer **50** and the intrinsic amorphous silicon layer **40** are photo etched using a second mask to have an island shape on the gate electrode **21**. As shown in FIGS. 12C and 12D, the gate pad and the data pad are also covered with the gate insulating layer **30**.

As shown in FIGS. 13A-13E, a metal layer made of chromium, aluminum alloy or molybdenum having thickness of around 500 Å or less is deposited, and etched using a third mask to form a data wire including a data line **60**, a source and a drain electrodes **61** and **62**, a data pad **63** and

a data line connector **64** and a pixel wire including pixel electrodes line **66** (in FIG. **5**) and pixel electrodes **65**. Then, the exposed portions of the doped amorphous silicon layer **50** are removed using the data wire as an etch mask to expose the intrinsic amorphous silicon layer **40**.

As shown in FIGS. **14A–14E**, a silicon nitride or an organic insulating material layer is deposited to a thickness of 1,500–2,600 Å to form a passivation layer **70**, and the passivation layer **70** is patterned to form contact holes **71**, **73** and **75** exposing the data line **60**, the data pad **63** and the data line connector **64** respectively. Contact holes **72** and **74** are also formed by removing portions of the gate insulating layer **30** and the passivation layer **70** on both of the gate pad **22** and the gate line connector **24**.

As shown in FIGS. **6–10**, a metal layer of 2,000–2,500 Å made of molybdenum, molybdenum alloy or aluminum alloy is deposited and patterned to form conductor patterns **80**, **83**, **85**, **82** and **84**. The conductor patterns **80**, **83**, **85**, **82** and **84** may have a double-layered structure.

An alignment layer is coated on the substrate and rubbed. The gate line connector and the data line connector are removed by cutting off their branches.

The liquid crystal display according to the second embodiment of the present invention, the thickness of the pixel electrode is preferably about 500 Å or less, and that of the redundant data wire is preferably about 2,000–2,500 Å. The thin pixel electrode enables the passivation layer to have flat surface and thus reduces the light leakage due to the non-uniform rubbing. The thick redundant data wire has relatively small resistance, and thus it reduces the resistance of the data wire as well as prevents the open of the data wire.

In the meantime, since the redundant data wire forms an upper layer of the pad region, a pad material which is not easily broken in the manufacturing process may be used for the redundant data wire in order to improve the contact characteristic between the pad and the external driving integrated circuits. ITO (indium tin oxide) is an example of a pad material.

The redundant wire may have a double-layered structure including an upper ITO layer, such that the contact characteristic between the pad and the external driving integrated circuits is much more improved.

The pixel wire may be formed of the same layer as the redundant data wire.

That is, as shown in FIGS. **15A–16E**. A gate wire including a gate line **20**, a gate electrode **21**, a gate pad **22** and a gate line connector **24** and a common signal wire including a common signal line **10** and common electrodes **11** are formed. A gate insulating layer **30**, a hydrogenated amorphous silicon layer **40** and an n+ hydrogenated amorphous silicon layer **50** are deposited in sequence. The doped amorphous silicon layer **50** and the intrinsic amorphous silicon layer **40** are photo etched. A data wire **60**, **61**, **62** and **63** is formed on the gate insulating layer **30**, and a passivation layer **70** having a contact hole **76** exposing the drain **500** Å or less. In this case, the pixel wire and the redundant data wires are preferably formed of a material suitable for pad such as chromium, molybdenum or molybdenum alloy.

In the above embodiments of the present invention, several small portions of the passivation layer on the data wire are removed, and the data wire and the redundant data wire are electrically connected through the removed portions. However, as shown in FIGS. **18–23**, a portion of the passivation layer **70** on the data wire **60**, **63** and **64** may be removed completely, and the redundant data wire **80**, **83** and **85** may be formed directly on the data wire **60**, **63** and **64** to

decrease the contact resistance between the data wire and the redundant data wire and to reduce the height difference between the upper surfaces of the redundant data wire and of the passivation layer.

In the second embodiment of the present invention, both the gate line connector and the data line connector are formed to have redundant wires, and the redundant gate line connector (or the longitudinal portion of the conductor pattern) and the redundant data line connector (or the transverse portion of the conductor pattern) which are formed of the same layer are short-circuited. However, one or both of the redundant gate line connector and the redundant data line connector may not be formed, and a conductor pattern connecting the data line connector and the gate line connector may be formed when the redundant data wire is formed.

Since the pixel electrode is formed thin in the liquid crystal displays according to the embodiments of the present invention, the height difference of the upper surfaces of the pixel electrodes and of the common electrodes is compensated by the relatively thick passivation layer formed on the pixel electrode. Therefore, the surfaces of the passivation layer and of the alignment layer thereon are flat and thus the uniform rubbing is possible. Accordingly, the contrast ratio increases due to the decrease of the light leakage. The data wire may have a open-free structure by forming the data wire as a double-layered structure or forming the redundant data wire. The manufacturing process is simple since only 5 masks are used. The contact characteristic between the driver IC (integrated circuit) and the pads is improved by using a pad material, which is not broken easily in the manufacturing process, as the pad or the redundant pad.

In the drawings and specification, there have been disclosed typical preferred embodiments of the invention and, although specific terms are employed, they are used in a generic and descriptive sense only and not for purposes of limitation, the scope of the invention being set forth in the following claims.

What is claimed is:

1. A liquid crystal display, comprising:
 - a substrate;
 - a gate line formed on the substrate;
 - a gate pad formed on the substrate and connected to an end portion of the gate line;
 - common electrodes which are formed on the substrate and separated from the gate line;
 - a gate insulating layer formed on the gate line, the gate pad and the common electrode;
 - a data line formed on the gate insulating layer;
 - a data pad which is formed on the gate insulating layer and connected to an end portion of the data line;
 - pixel electrodes which are formed on the gate insulating layer, and spaced apart from the common electrode;
 - a thin film transistor electrically connected to the gate line, the data line and the pixel electrode;
 - a passivation layer which covers the data line, the pixel electrode and the thin film transistor, and has a first contact hole exposing the data pad and a second contact hole exposing the gate pad along with the gate insulating layer;
 - a first redundant pad which is formed on the passivation layer and contacts the data pad through the first contact hole;
 - a second redundant pad which is formed on the passivation layer and contacts the gate pad through the second contact hole;

wherein the first or the second redundant pads include aluminum or chromium.

2. A liquid crystal display, comprising:

- a substrate;
- a gate line formed on the substrate;
- a gate pad formed on the substrate and connected to an end portion of the gate line;
- common electrodes which are formed on the substrate and separated from the gate line;
- a gate insulating layer formed on the gate line, the gate pad and the common electrode;
- a data line formed on the gate insulating layer;
- a data pad which is formed on the gate insulating layer and connected to an end portion of the data line;
- pixel electrodes which are formed on the gate insulating layer, and spaced apart from the common electrode;
- a thin film transistor electrically connected to the gate line, the data line and the pixel electrode;
- a passivation layer which covers the data line, the pixel electrode and the thin film transistor, and has a first contact hole exposing the data pad and a second contact hole exposing the gate pad along with the gate insulating layer;
- a first redundant pad which is formed on the passivation layer and contacts the data pad through the first contact hole;

a second redundant pad which is formed on the passivation layer and contacts the gate pad through the second contact hole, wherein the pixel and the common electrodes are alternately formed.

3. A liquid crystal display, comprising:

- a substrate;
- a gate line formed on the substrate;
- a gate pad formed on the substrate and connected to an end portion of the gate line;
- common electrodes which are formed on the substrate and separated from the gate line;
- a gate insulating layer formed on the gate line, the gate pad and the common electrode;
- a data line formed on the gate insulating layer;
- a data pad which is formed on the gate insulating layer and connected to an end portion of the data line;
- pixel electrodes which are formed on the gate insulating layer, and spaced apart from the common electrode;
- a thin film transistor electrically connected to the gate line, the data line and the pixel electrode;
- a passivation layer which covers the data line, the pixel electrode and the thin film transistor, and has a first contact hole exposing the data pad and a second contact hole exposing the gate pad along with the gate insulating layer;
- a redundant pad which is formed on the passivation layer and contacts the data pad through the first contact hole.

4. A liquid crystal display, comprising:

- a substrate;
- a gate line formed on the substrate;
- a gate pad formed on the substrate and connected to an end portion of the gate line;
- common electrodes which are formed on the substrate and separated from the gate line;
- a gate insulating layer formed on the gate line, the gate pad and the common electrode;

- a data line formed on the gate insulating layer;
- a data pad which is formed on the gate insulating layer and connected to an end portion of the data line;
- pixel electrodes which are formed on the gate insulating layer, and spaced apart from the common electrode;
- a thin film transistor electrically connected to the gate line, the data line and the pixel electrode;
- a passivation layer which covers the data line, the pixel electrode and the thin film transistor, and has a first contact hole exposing the data pad and a second contact hole exposing the gate pad along with the gate insulating layer; a redundant pad which is formed on the passivation layer and contacts the gate pad through the second contact hole.

5. A liquid crystal display, comprising:

- a substrate;
- a gate line formed on the substrate;
- a gate pad formed on the substrate and connected to an end portion of the gate line;
- common electrodes which are formed on the substrate and separated from the gate line;
- a gate insulating layer formed on the gate line, the gate pad and the common electrode;
- a data line formed on the gate insulating layer;
- a data pad which is formed on the gate insulating layer and connected to an end portion of the data line;
- pixel electrodes which are formed on the gate insulating layer, and spaced apart from the common electrode;
- a thin film transistor electrically connected to the gate line, the data line and the pixel electrode;
- a passivation layer which covers the data line, the pixel electrode and the thin film transistor, and has a first contact hole exposing the data pad and a second contact hole exposing the gate pad along with the gate insulating layer;
- a first redundant pad which is formed on the passivation layer and contacts the data pad through the first contact hole;
- a second redundant pad which is formed on the passivation layer and contacts the gate pad through the second contact hole,

wherein the portions of the common electrodes are closer to the data line than the pixel electrodes.

6. A liquid crystal display, comprising:

- a substrate;
- a gate line formed on the substrate;
- a gate pad formed on the substrate and connected to an end portion of the gate line;
- common electrodes which are formed on the substrate and separated from the gate line;
- a common electrode line which is formed on the substrate and connected to the common electrodes;
- a gate insulating layer formed on the gate line, the gate pad and the common electrode;
- a data line formed on the gate insulating layer;
- a data pad which is formed on the gate insulating layer and connected to an end portion of the data line;
- pixel electrodes which are formed on the gate insulating layer, and spaced apart from the common electrode;

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a pixel electrode line which is formed on the gate insulating layer, and connected to the pixel electrodes;
 a thin film transistor electrically connected to the gate line, the data line and the pixel electrode;
 a passivation layer which covers the data line, the pixel electrode and the thin film transistor, and has a first contact hole exposing the data pad and a second contact hole exposing the gate pad along with the gate insulating layer;
 a first redundant pad which is formed on the passivation layer and contacts the data pad through the first contact hole;
 a second redundant pad which is formed on the passivation layer and contacts the gate pad through the second contact hole, wherein the common electrode line and the pixel electrode line overlap to each other.

7. The liquid crystal display claimed to claim 6, wherein at least one boundary of the common electrode line overlap the pixel electrode line.

8. A liquid crystal display, comprising:
 a substrate;
 a gate line formed on the substrate;
 a gate pad formed on the substrate and electrically connected to an end portion of the gate line;
 common electrodes which are formed on the substrate and separated from the gate line;
 a gate insulating layer covering the gate line, the gate pad and the common electrodes and exposing at least a portion of the gate pad;
 a semiconductor layer formed on the gate insulating layer;

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source and drain electrodes contacted with the semiconductor layer;
 a data line electrically connected to the source electrode;
 a data pad electrically connected to an end portion of the data line;
 pixel electrodes electrically connected to the drain electrode, and parallel to the common electrode;
 a passivation layer covering at least a portion of the data line, the drain electrode and the source electrode, and exposing at least a portion of the gate pad exposed through the gate insulating layer and at least a portion of the data pad;
 a first redundant pattern formed on the passivation layer and electrically connected with the exposed portion of the gate pad; and
 a second redundant pattern formed on the passivation layer and electrically connected with the exposed portion of the data pad.

9. The liquid crystal display of claim 8, wherein the semiconductor layer contains ohmic contact layers.

10. The liquid crystal display of claim 8, wherein a portion of the common electrodes and a portion of the pixel electrodes are overlap.

11. The liquid crystal display of claim 8, wherein the data line is closer to the common electrodes than the pixel electrodes.

12. The liquid crystal display of claim 9, wherein the source and the drain electrodes contact with the semiconductor layer through ohmic contact layers.

13. The liquid crystal display of claim 8, wherein the passivation layer covers the pixel electrodes.

* * * * *

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[标]申请(专利权)人(译)	宋军HO LEE KYEONG NAM		
申请(专利权)人(译)	宋军-HO 李KYEONG-NAM		
当前申请(专利权)人(译)	SAMSUNG ELECTRONICS CO. , LTD.		
[标]发明人	SONG JUN HO LEE KYEONG NAM		
发明人	SONG, JUN-HO LEE, KYEONG-NAM		
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摘要(译)

包括栅极线，栅电极，栅极焊盘和栅极线连接器以及公共信号线的栅极线形成在基板上，并且栅极绝缘层形成在栅极线和公共信号线之上。在栅极绝缘层上依次形成半导体层和欧姆接触层，在其上形成包括源极和漏极的数据线，数据线，数据焊盘和数据线连接器以及像素电极。数据线和像素电极的厚度等于或小于500埃。在数据线和像素电极上形成钝化层，在其上形成冗余数据线，并形成冗余栅极焊盘和冗余栅极线连接器。冗余数据线通过钝化层中的接触孔电连接到数据线，冗余栅极焊盘和冗余栅极线连接器分别通过接触孔电连接到栅极焊盘和栅极线连接器。钝化层和栅极绝缘层。冗余栅极线连接器和冗余数据线连接器彼此连接以使栅极和数据线短路。在形成并摩擦取向层之后，切掉面板的边缘以移除栅极线连接器和数据线连接器。

